Dual Wavelength InGaAs Avalanche Photodiode Preamplifier Module

CMC Electronics' 264-339822 series uses an InGaAs APD with low ionization ratio of 0.2, with a built-in preamplifier, enabling optimum signal to noise performance.

The APD is coupled to a GaAs FET input trans-impedance amplifier in a 12-lead TO-8 package. The amplifier has an overload input protection circuit which sustains high optical power exposure with a very fast recovery time. The internal temperature can be monitored via an embedded thermal sensor located close to the APD. The module is designed for a 100-ohm output load connection (AC or DC coupled, as required by design).

Customizations such as bandwidth selection, NEP screening, responsivity optimization and packaging are available, to fit your system design needs.

Features

- 200 µm InGaAs APD
- 50-100 MHz built-in trans-impedance amplifier
- Spectral Response: 1050-1600nm (typical use: 1570nm)
- Low k of 0.2 (Low noise) InGaAs APD
- Low Noise Equivalent Power (NEP)
- Fast Overload Recovery
- High Quantum Efficiency
- Hermetically Sealed TO-8 Package
- ITAR free

Applications

- Range Finding
- LIDAR
- Instrumentation
- Laser Profiling
- Free–Space Communications
- Industrial
- Photometry

Table 1. Electro-Optical Characteristics

Unless otherwise specified: T_A = 25°C, V+ = 5 V, V- = -5 V, R_L = 100 Ω AC, λ = 1570 nm +/- 10 nm (Externally AC coupled through 4.7µF)

Parameter	Min.	Typ.	Max.	Units
Active area		200		µm
Operating Voltage (Note 1)	40	54	85	V
Temperature coefficient of V_{OP}		0.07		V/˚C
ADP dark current		20	55	nA
Responsivity		580		kV/W
Noise equivalent power (Note 2)				
1570 nm [T_{case}=25°C]		110	135	fW/√Hz
1570 nm [T_{case}=85°C]		255	525	fW/√Hz
Output impedance		10		Ω
Bandwidth	50	60		MHz
Rise time (10-90%)		6		ns
Fall time (90-10%)		6		ns
Linear output voltage swing (Pulse)	1.5	2.5	4.0	V
Output offset voltage	-0.75	-0.45	0	V
Thermal sensor (1N914 diode) at 5 mA		645		mV
Overload recovery for optical power input signal of 1 mW, 20 ns pulse width: V_{out} → 200 ns after pulse start			250	mV
V_{out} → 1 µs after pulse start			40	mV
Hybrid Supply current V_POS (pin 12)	25		35	mA
V_NEG (pin 3)	-20		-10	mA

Notes:
1. Each APD receivers will have its individual V_{OP} (provided on its production tests report).
2. NEP values for +85°C are by design and are for reference only. No test values provided on individual test reports. Integration of the noise calculation is based on minimum bandwidth.

Table 2. Absolute-Maximum Ratings, Limiting Values

Parameter	Min.	Max.	Units
APD breakdown, Maximum voltage [HV_POS (pin4)] (Note 1)		105	V
Recommended overcurrent limit		100	µA
Input Voltage Positive Supply [V_POS (+5V) (pin12)]	+4.8	+6.0	V
Input Voltage Negative Supply [V_NEG (-5V) (pin3)]	-4.8	-6.0	V
Maximum Optical Power, CW		10	µW
Peak value, 20ns pulses < 100Hz		100	kW/cm^2
Temperature sensor			
Sensor V_{in} → TS_AN (pin 8)	1	10	mA
Sensor output → TS_CA (pin 9)	1	10	mA
Operating Temperature	-40	85	°C
Storage Temperature	-55	125	°C

Note: 1. Absolute maximum over the product Temperature Operating Range (-40°C to +85°C).

Figure 1. CMC 264-339822 Series block diagram

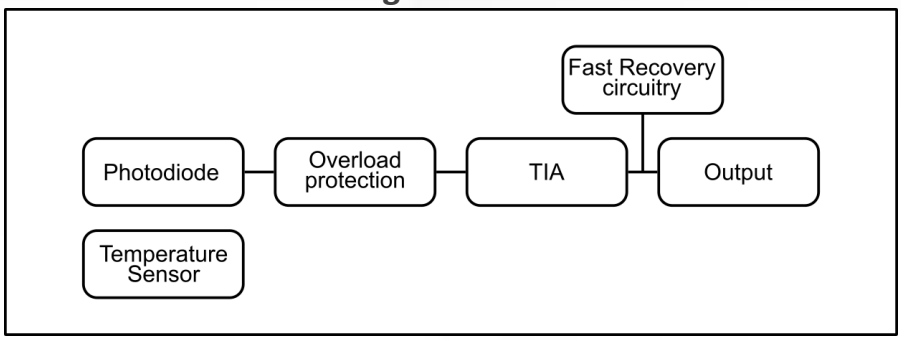
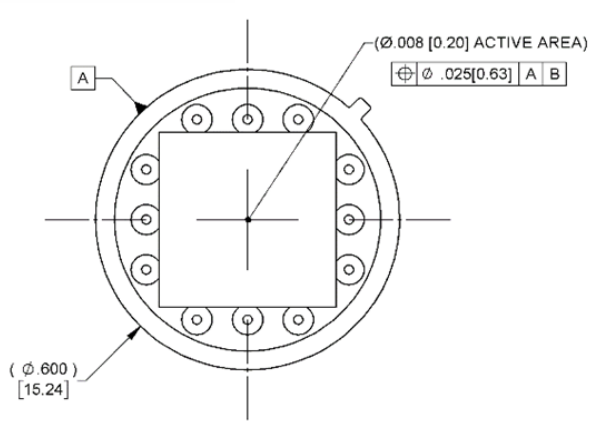
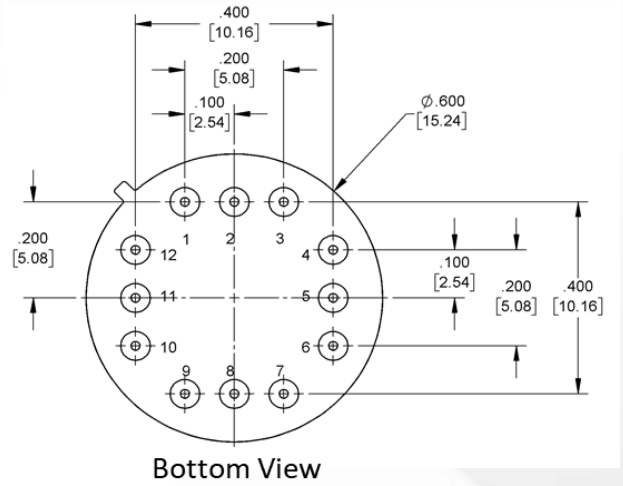
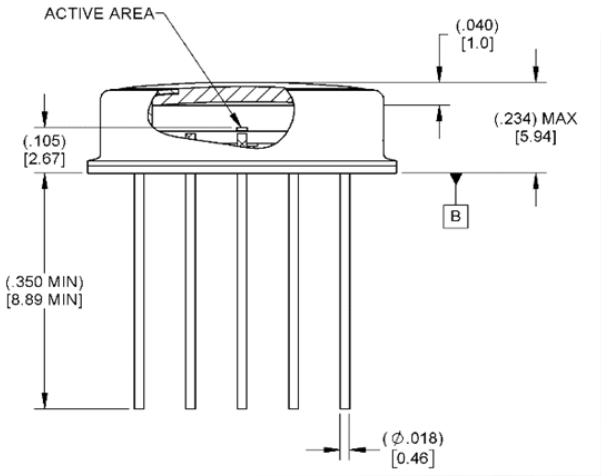


Figure 2. Package Dimension and Pinout

Unless otherwise specified, dimensions are in inches (mm) and are for reference only.







1	OUTPUT	7	GND
2	NC	8	TSensor ANODE
3	V_NEG (-5V)	9	Tsensor CATHODE
4	HV_POSITIVE	10	GND
5	NC	11	NC
6	GND	12	V_POS (+5V)

VAR Options

-001	InGaAs APD 200 µm, 50-100 MHz TIA

For more information, visit www.cmcelectronics.ca or email us at opto@cmcelectronics.ca

For information purposes only. To accommodate product improvements, specifications are subject to change without notice.

APPROVED FOR PUBLIC RELEASE; DISTRIBUTION IS UNLIMITED
CMC-MEG-OPTO822-VAR
September 2024